

PATENT  
W&B Ref. No.: INF 2070-US  
Atty. Dkt. No. INFN/WB0041

**IN THE SPECIFICATION:**

Please replace paragraph [0011] with the following amended paragraph:

[0011] In order to realize the vertically arranged selection transistors, a drive region, to which the drive signal is applied, may be arranged above the trench capacitor. The drive region is preferably ~~configured~~ configured in such a way that it may simultaneously serve as a gate region for the first and the second selection transistors.

Please replace paragraph [0020] with the following amended paragraph:

[0020] The first bit line BL1 and the second bit line BL2 of the bit line pair BLP are connected to a sense amplifier 1 at one end. The sense amplifier is ~~configured~~ configured in such a way that it detects a charge difference between the two bit lines BL1, BL2 of the bit line pair BLP and increases the potential of the bit line with the higher charge and decreases the potential of the bit line with the lower charge. By virtue of the fact that the charge stored in the storage capacitor is applied to both bit lines equally and simultaneously, the result is a symmetrical opposite signal profile around the center potential on the two bit lines.